



800μm Si APD – IR enhanced (P/N.: ASi-800-02-01)

Features

- 800μm active area
- Responsivity enhanced for 1064nm

Absolute Maximum Ratings

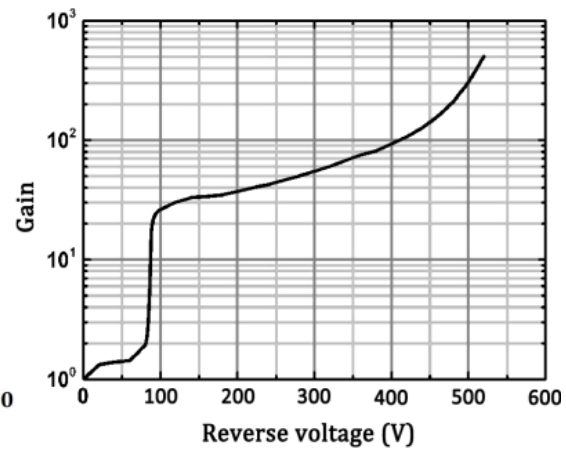
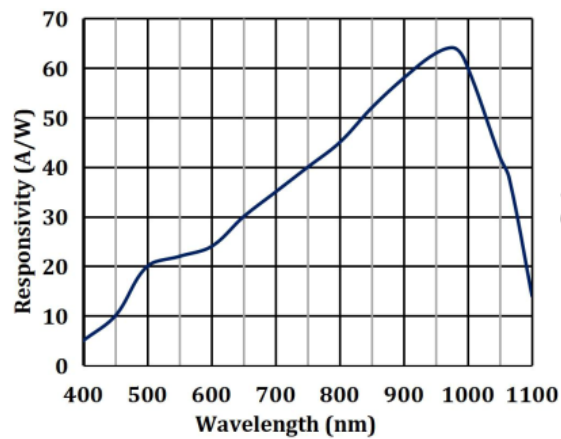
Parameter	Symbol	Min	Typ	Max	Unit
Operating Case Temperature	T _C	-50	-	85	°C
Storage Temperature	T _{STG}	-55	-	100	°C

Opto-Electrical Characteristics

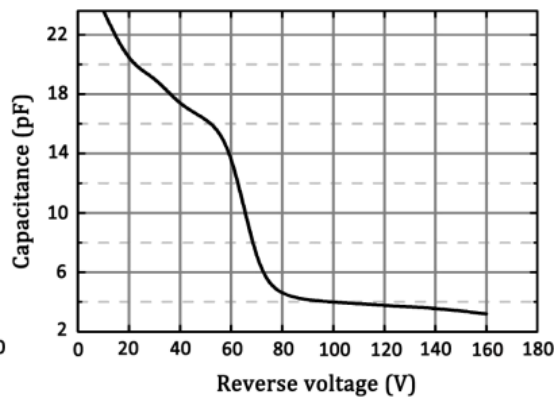
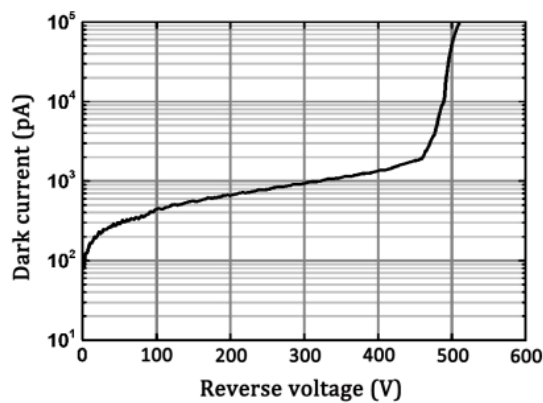
Parameter	Symbol	Min	Typ	Max	Unit	Notes
Wavelength Range	λ	400		1100	nm	
Reverse Breakdown Voltage	V _{BR}	220		580	V	I _D = 10μA
Risetime (@ 1064nm)	τ_{rise}	-	3	-	ns	50Ohm, M = 100
Spectral Responsivity	S	-	0.38	-	A/W	1064nm, M = 1
Multiplied Dark Current	I _{DM}	-	4	20	nA	M = 100
Capacitance	C _J	-	1.5	1.7	pF	M = 100
Temperature coeff of V _{BR}	$\Delta V/\Delta T$	-	2.3	-	V/°C	T = 25°C



Responsivity and gain performances



Dark current and Capacitance



Dimensional outlines (unit = mm)

TO

Package can be customized

